

PRODUCT/PROCESS CHANGE NOTIFICATION

PCN IPG-DIS/14/8337 Dated 19 Feb 2014

Power Rectifiers Additional Assembly and Test Location in China for DPAK package

Table 1. Change Implementation Schedule

Forecasted implementation date for change	12-Feb-2014
Forecasted availability date of samples for customer	12-Feb-2014
Forecasted date for STMicroelectronics change Qualification Plan results availability	12-Feb-2014
Estimated date of changed product first shipment	21-May-2014

Table 2. Change Identification

Product Identification (Product Family/Commercial Product)	Selected Power Rectifiers in DPAK package	
Type of change	Assembly additional location	
Reason for change	to increase ST's manufacturing capacity	
Description of the change	see attached	
Change Product Identification	marking, internal codification and QA number	
Manufacturing Location(s)		

Tab	le 3	List	of .	Attac	hments	3

Customer Part numbers list	
Qualification Plan results	

Customer Acknowledgement of Receipt	PCN IPG-DIS/14/8337
Please sign and return to STMicroelectronics Sales Office	Dated 19 Feb 2014
□ Qualification Plan Denied	Name:
□ Qualification Plan Approved	Title:
	Company:
□ Change Denied	Date:
□ Change Approved	Signature:
Remark	
i e e e e e e e e e e e e e e e e e e e	

47/.

DOCUMENT APPROVAL

Name	Function
Paris, Eric	Marketing Manager
Duclos, Franck	Product Manager
Cazaubon, Guy	Q.A. Manager

A7/.



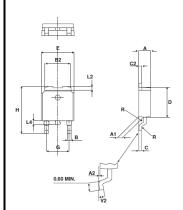
(1) IPG: Industrial & Power Group - ASD: Application Specific Device – IPAD™: Integrated Passive and Active Devices

PCN Product/Process Change Notification

Power Rectifiers Additional Assembly and Test Location in China for DPAK package Notification number: IPG-DIS/14/8337 12/02/2014 **Issue Date** Aline AUGIS Issued by Product series affected by the change **Power Schottky Diodes** STPS15H100CB-TR STPS5H100B-TR **Ultrafast Diodes** STTH5R06B-TR STTH506B-TR STTH1003SB-TR Type of change Additional assembly package location

Description of the change

STMicroelectronics decided to **expand the manufacturing capacity Power Rectifiers** (Power Schottky and Ultrafast Diodes) housed in **DPAK package** with one **additional assembly** and **test plant** in China. In order to cover both manufacturing locations DPAK package outline dimensions, the package dimension table of the impacted products will be updated as below:



Ori	ginal DPAK dimensions	specified in datasheet	s N	EW DPAK dimensions	specified in datasheets
	Dimensions (mm)			Dimensi	ons (mm)
	Min.	Max.		Min.	Max.
Α	2.2	2.4	Α	2.18	2.4
Α1	0.9	1.1	Α1	0.9	1.1
Α2	0.03	0.23	A2	0.03	0.23
В	0.64	0.9	В	0.64	0.9
B2	5.2	5.4	B2	4.95	5.46
С	0.45	0.6	С	0.45	0.61
C2	0.48	0.6	C2	0.46	0.6
D	6	6.2	D	5.97	6.22
E	6.4	6.6	Ε	6.35	6.73
G	4.4	4.6	G	4.4	4.7
Н	9.35	10.1	Н	9.35	10.34
L2	0.80	typ.	L2		1.27
L4	0.6	1	L4	0.6	1.02
V2	0°	8°	V2	0°	8°

Reason for change

This additional multi-sourcing will increase our **manufacturing capacity** for a better service on the considered **Power Rectifier** devices.

Issue date 12-02-2014 1/3

STMicroelectronics IPG - ASD & IPAD™ Division¹ BU Diodes and Rectifiers



(1) IPG: Industrial & Power Group - ASD: Application Specific Device – IPAD™: Integrated Passive and Active Devices

Former versus changed product:	The changed products do not present modified electrical, parameters, leaving unchanged the current information published in the product datasheet
	The Moisture Sensitivity Level of the part (according to the IPC/JEDEC JSTD-020D standard) remains unchanged.
	The footprint recommended by ST remains the same.
	There is no change in the packing modes and the standard delivery quantities either.

Disposition of former products

As the purpose is to expand the manufacturing capacity, shipments of the products processed in the initial test and assembly site will continue.

Marking and traceability

Parts produced in the new China location are differentiated by their marking as indicated below

		Date code marking	
Assembly location	Assy plant code	Assy year	Assy week
China 1 (ST)	GK	 Y (1 digit indicating 	WW (2 digits
New location : China 2 (subco)	GE	the year)	indicating the week number)

Traceability for the implemented change will be ensured by an internal codification and by the Q.A. number.

Qualification complete date	27-Nov-2012
-----------------------------	-------------

Forecasted sample availability

Product family	Sub-family	Commercial part Number	Availability date
Diodes & Rectifiers	Power Schottky	STPS15H100CB-TR	
Diodes & Rectifiers	Power Schottky	STPS5H100B-TR	
Diodes & Rectifiers	Ultrafast Diodes	STTH5R06B-TR	Upon request with 4 weeks of delay
Diodes & Rectifiers	Ultrafast Diodes	STTH506B-TR	_
Diodes & Rectifiers	Ultrafast Diodes	STTH1003SB-TR	-

Issue date 12-02-2014 2/3

STMicroelectronics IPG - ASD & IPAD™ Division¹ BU Diodes and Rectifiers



(1) IPG: Industrial & Power Group - ASD: Application Specific Device – IPAD™: Integrated Passive and Active Devices

Change implementation schedule				
Sales types	Estimated production start	Estimated first shipments		
All	Week 10 - 2014	Week 20 - 2014		
Comments:				
Customer's feedback				
Please contact your local ST sales representative or quality contact for requests concerning this change notification.				
Absence of acknowledgement of this PCN within 30 days of receipt will constitute acceptance of the change Absence of additional response within 90 days of receipt of this PCN will constitute acceptance of the change				
Qualification program and results	QRP11259QRP	r.		

Issue date 12-02-2014 3/3



Qualification of ECOPACK®2 resin for Rectifiers products in DPAK package

General Information

Product Line Rectifiers

Rectifiers in DPAK package:

Product Description ECOPACK®2 resin

Product Group APM

Product division ASD & IPAD

Package DPAK Maturity level step DPAK Qualified

Wafer fab

Locations

STM Tours (France)
STM Singapore

Assembly plant

STM Long Gang (China)
Subcontractor (China)

Reliability Lab STM Tours (France)

DOCUMENT INFORMATION

V	ersion	Date	Pages	Prepared by	Comment
1.0		21-Nov-2011	8	I. BALLON	First issue Qualification of Rectifiers products in DPAK package at STM Long Gang: ECOPACK®2 resin
	2.0	03-Dec-2012	9	I. BALLON	Qualification of DPAK package at subcontractor in China: ECOPACK®2 resin

Note: This report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the potential reliability risks during the product life using a set of defined test methods.

This report does not imply for STMicroelectronics expressly or implicitly any contractual obligations other than as set forth in STMicroelectronics general terms and conditions of Sale. This report and its contents shall not be disclosed to a third party without previous written agreement from STMicroelectronics.





TABLE OF CONTENTS

1	APPL	LICABLE AND REFERENCE DOCUMENTS	3
2	GLO	SSARY	3
		ABILITY EVALUATION OVERVIEW	
	3.1	Objectives	
	3.2	CONCLUSION	
4		CE CHARACTERISTICS	
	4.1	DEVICE DESCRIPTION	
	4.2	CONSTRUCTION NOTE	4
5	TEST	TS RESULTS SUMMARY	5
		Test vehicles	
	5.2	TEST PLAN AND RESULTS SUMMARY	5
6		EXES	
	6.1	DEVICE DETAILS	7
	6.2	PACKAGE OUTLINE/MECHANICAL DATA	
	6.3	TESTS DESCRIPTION	c



ST Restricted

1 APPLICABLE AND REFERENCE DOCUMENTS

Document reference	Short description
JESD47	Stress-Test-Driven Qualification of Integrated Circuits
FMEA	8315678 - 8320100
RER	1126008 (ST Long Gang in China) – 1126011 (subcontractor in China)

2 GLOSSARY

DUT	Device Under Test
PCB	Printed Circuit Board
SS	Sample Size
HTRB	High Temperature Reverse Bias
TC	Temperature Cycling
PCT	Pressure Cooker Test (Pressure Pot)
ТНВ	Temperature Humidity Bias
SD	Solderability

3 RELIABILITY EVALUATION OVERVIEW

Objectives 3.1

The objective of this report is to qualify "Halogen-Free" encapsulation molding compound for Rectifiers housed in DPAK package at ST Long Gang (China) and subcontractor in China.

The product series are listed below.

Product sub-Family	DPAK series
Power Schottky Diodes	STPSxxxB(-TR) STPSxxxCB(-TR) STPSxxHxxB(-TR) STPSxxHxxCB(-TR) STPSxxLxxB(-TR) STPSxxLxxCB(-TR)
Ultrafast Diodes	STTHxxxB(-TR) STTHxxxCB(-TR) STTHxxxSB(-TR) STTHxxLCDxxSB(-TR) STTHxxPxxSB(-TR) STTHxxRxxB(-TR) STTHxxRxxB(-TR)

The reliability methodology used in this qualification follows the JESD47-G: «Stress Test Driven Qualification Methodology».

3.2 Conclusion

The perimeter addressed in this campaign qualifies the production of Rectifiers housed in DPAK package at ST Long Gang (China) and subcontractor in China with the "Halogen-Free" encapsulation molding compound. Reliability tests are positive.

Qualification Plan requirements have been fulfilled without exception. Reliability tests have shown that the devices behave correctly against environmental tests (no failure). Moreover, the stability of electrical parameters during the accelerated tests demonstrates the robustness of the products and safe operation, which is consequently expected during their lifetime.

4 DEVICE CHARACTERISTICS

4.1 **Device description**

• Rectifiers in DPAK package with ECOPACK®2 Molding compound assembled at ST Long Gang (China) plant and subcontractor plant in China.

4.2 Construction note

	Rectifiers in DPAK package with new ECOPACK®2 Molding compound
Wafer/Die fab. information	
Wafer fab manufacturing location	STM Singapore STM Tours (France)
Wafer Testing (EWS) information	
Electrical testing manufacturing location	STM Singapore STM Tours (France)
Assembly information	
Assembly site	STM Long Gang (China) Subcontractor in China
Package description	DPAK
Molding compound	ECOPACK®2 ("Halogen-free") molding compound
Frame material	Copper
Die attach process	Soft solder
Die attach material	Preform Pb/Sn/Ag
Wire bonding process	Ultra Sonic wire bonding
Wires bonding materials	Aluminium
Lead finishing process	Plating
Lead finishing material	Tin (Sn 100%)
Final testing information	
Testing location	STM Long Gang (China) Subcontractor in China



5 TESTS RESULTS SUMMARY

5.1 **Test vehicles**

Lot #	Process/ Package	Assembly plant	Product Family	Product	
1			Power Schottky	STPS15H100CB	
2	DPAK		Turboswitch	STTH512B	
3	DFAR		Power Schottky	STPS15H100CB	
4			Turboswitch	STTH5R06B	
5		ST China	Power Schottky	STPS3045CG	
6	D²PAK	ST CIIIIa	Power Schottky	STPS30170CG	
7	D-PAR		Ultrafast	STTH2004SG	
8			Power Schottky	STPS41H100CG	
9	DPAK		Turboswitch	STTH512B	
10	DPAK		Power Schottky	STPS15H100CB	
11 / 15			Dowar Schottley	STPS15L45CB	
12 / 16	DPAK	Subcentractor (China)	Power Schottky	STPS15H100CB	
13 / 17	DFAK	Subcontractor (China)	Ultrafast	STTH512B	
14 / 18			Ulitalast	STTH5R06B	

5.2 **Test plan and results summary**

Die Oriented Tests

I						Failure/SS					
	Test	РС	Std ref.	Conditions	SS	Steps	Lots 5 to 10	Lot 12	Lot 13	Lot 14	Note
Ī			IECDOO			168 H	0/77	0/76	0/76	0/77	
	HTRB	Ν	JESD22 A-108	Tj, $Vr = 0.8xVrrm$	691	500 H	0/77	0/76	0/76	0/77	
			A-106			1000 H	0/77	0/76	0/76	0/77	

Package Oriented Tests

Package Or	ient	ea rests									
Toot	РС	Std ref.	Conditions	SS	Ctono			Failure/S	SS		Note
Test	FC	Sta rei.	Conditions	33	Steps	Lot 1	Lot 2	Lot 11	Lot	:13	Note
		JESD22	Ta = 85°C, RH = 85%, Vr =		168 H	0/25	0/77	0/24	0/2	24	
THB	Υ		0.8xVrrm	198	500 H	0/25	0/77	0/24	0/2	24	
		A-101	or 100V max		1000 H	0/25	0/77	0/24	0/2	24	
				00	Ctono			Failure/S	SS		Nata
				SS	Steps	Lot 3	Lot 4	Lot 11	Lot 12	Lot 14	Note
					100 cy	0/25	0/25	0/25	0/25	0/25	
					500 cy	0/25	0/25	0/25	0/25	0/25	
TC	_	JESD22	Ta = -55°C to 150°C	227	Stone			Failure/S	SS		
10	ı	A-104	1a = -55 C to 150 C	221	Steps	Lot 15	Lot 16	Lot 17	Lot 18		
					100 cy	0/28	0/26	0/23	0/25		
					500 cy	0/28	0/26	0/23	0/25		



Test	РС	Std ref.	Conditions	ss	Steps	Failure/SS					Note			
Test	PC	Stu rei.	Conditions		Steps	Lot 1	Lot 2	Lot 11	Lot 12	Lot 14	NOLE			
					96hrs	0/24	0/77	0/25	0/25	0/25				
PCT	_	JESD22	121°C, 100% RH, 2bars		276	276	276	276	276	Steps		Failure/SS		
FCI	ı	A-102	121 C, 100 /6 KH, 20als	270	Siehs	Lot 15	Lot 16	Lot 17	Lo	ot 18				
					96hrs	0/25	0/25	0/25	0.	/25				

Test	РС	Std ref.	Conditions	SS	S Steps	Failure/SS				Note	
						Lot 1	Lot 2	Lot 11	Lot 12	Lot 14	
			245°C SnAgCu bath Dry aging	50		0/10	0/10	0/10	0/10	0/10	
			245°C SnAgCu bath Wet aging	50		0/10	0/10	0/10	0/10	0/10	
Solderability	NI.	L STD 000		SS	Steps			Failure/S	SS		Note
Solderability	IN	J-31D-002		o o	Steps	Lot 1	Lot 2	Lot 11	Lot 12	Lot 14	Note
			220°C SnPb bath Dry aging	50		0/10	0/10	0/10	0/10	0/10	
			220°C SnPb bath Wet aging	50		0/10	0/10	0/10	0/10	0/10	



6 ANNEXES

6.1 **Device details**

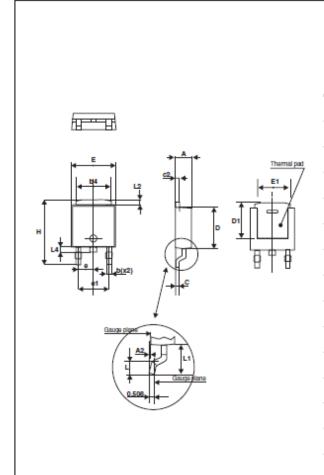
6.1.1 Pin connection and bonding diagram

		Pin connection	
Package	For Single diode configuration STPSxxxxB STTHxxxxB	For Single diode configuration STPSxxxxSB STTHxxxxSB	For Double diodes configuration STPSxxxxCB STTHxxxxCB
	А —▶ κ	А	A1 · K
DPAK	K NC A	K A A	A1



6.2 Package outline/Mechanical data

DPAK dimensions



	Dimensions			
Ref.	Millimeters		Inches	
	Min.	Max.	Min.	Max.
Α	2.18	2.39	0.085	0.94
A1	0.90	1.10	0.035	0.043
A2	0.03	0.23	0.001	0.009
В	0.64	0.89	0.025	0.035
B2	4.95	5.46	0.194	0.214
С	0.46	0.61	0.018	0.024
C2	0.46	0.60	0.018	0.023
D	5.97	6.22	0.235	0.244
D1	5.0		0.196	
Е	6.35	6.73	0.25	0.264
E1	4.32		0.170	
e1	4.40	4.7	0.173	0.185
Н	9.35	10.34	0.368	0.407
L	1.0	1.78	0.039	0.070
L2		1.27		0.05
L4		1.01		0.039



6.3 **Tests description**

Test name	Description	Purpose			
Die Oriented					
HTRB High Temperature Reverse Bias HTFB / HTGB High Temperature Forward (Gate) Bias	The device is stressed in static configuration, trying to satisfy as much as possible the following conditions: low power dissipation; max. supply voltage compatible with diffusion process and internal circuitry limitations;	To determine the effects of bias conditions and temperature on solid state devices over time. It simulates the devices' operating condition in an accelerated way. To maximize the electrical field across either reverse-biased junctions or dielectric layers, in order to investigate the failure modes linked to mobile contamination, oxide ageing, layout sensitivity to surface effects.			
Package Oriented					
TC Temperature Cycling	The device is submitted to cycled temperature excursions, between a hot and a cold chamber in air atmosphere.	To investigate failure modes related to the thermo-mechanical stress induced by the different thermal expansion of the materials interacting in the die-package system. Typical failure modes are linked to metal displacement, dielectric cracking, molding compound delamination, wire-bonds failure, die-attach layer degradation.			
THB Temperature Humidity Bias	The device is biased in static configuration minimizing its internal power dissipation, and stored at controlled conditions of ambient temperature and relative humidity.	To evaluate the package moisture resistance with electrical field applied, both electrolytic and galvanic corrosion are put in evidence.			
AC/PCT Auto Clave (Pressure Pot)		To investigate corrosion phenomena affecting die or package materials, related to chemical contamination and package hermeticity.			

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

ST PRODUCTS ARE NOT DESIGNED OR AUTHORIZED FOR USE IN: (A) SAFETY CRITICAL APPLICATIONS SUCH AS LIFE SUPPORTING, ACTIVE IMPLANTED DEVICES OR SYSTEMS WITH PRODUCT FUNCTIONAL SAFETY REQUIREMENTS; (B) AERONAUTIC APPLICATIONS; (C) AUTOMOTIVE APPLICATIONS OR ENVIRONMENTS, AND/OR (D) AEROSPACE APPLICATIONS OR ENVIRONMENTS. WHERE ST PRODUCTS ARE NOT DESIGNED FOR SUCH USE, THE PURCHASER SHALL USE PRODUCTS AT PURCHASER'S SOLE RISK, EVEN IF ST HAS BEEN INFORMED IN WRITING OF SUCH USAGE, UNLESS A PRODUCT IS EXPRESSLY DESIGNATED BY ST AS BEING INTENDED FOR "AUTOMOTIVE, AUTOMOTIVE SAFETY OR MEDICAL" INDUSTRY DOMAINS ACCORDING TO ST PRODUCT DESIGN SPECIFICATIONS. PRODUCTS FORMALLY ESCC, QML OR JAN QUALIFIED ARE DEEMED SUITABLE FOR USE IN AEROSPACE BY THE CORRESPONDING GOVERNMENTAL AGENCY.

RESTRICTIONS OF USE AND CONFIDENTIALITY OBLIGATIONS:

THIS DOCUMENT AND ITS ANNEXES CONTAIN ST PROPRIETARY AND CONFIDENTIAL INFORMATION. THE DISCLOSURE, DISTRIBUTION, PUBLICATION OF WHATSOEVER NATURE OR USE FOR ANY OTHER PURPOSE THAN PROVIDED IN THIS DOCUMENT OF ANY INFORMATION CONTAINED IN THIS DOCUMENT AND ITS ANNEXES IS SUBMITTED TO ST PRIOR EXPRESS AUTHORIZATION. ANY UNAUTHORIZED REVIEW, USE, DISCLOSURE OR DISTRIBUTION OF SUCH INFORMATION IS EXPRESSLY PROHIBITED.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners

© 2014 STMicroelectronics - All rights reserved.

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

